M1MA151AT1, M1MA152AT1

Preferred Device

Single Silicon Switching Diodes

These Silicon Epitaxial Planar Diodes are designed for use in ultra high speed switching applications. These devices are housed in the SC–59 package which is designed for low power surface mount applications.

Features

- Fast t_{rr} , < 3.0 ns
- Low C_D, < 2.0 pF
- Pb–Free Packages are Available

MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Rating		Symbol	Value	Unit
Reverse Voltage	M1MA151AT1 M1MA152AT1	V _R	40 80	Vdc
Peak Reverse Voltage	M1MA151AT1 M1MA152AT1	V _{RM}	40 80	Vdc
Forward Current		١ _F	100	mAdc
Peak Forward Current		I _{FM}	225	mAdc
Peak Forward Surge Curre	ent	I _{FSM} (Note 1)	500	mAdc

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation	PD	200	mW
Junction Temperature	Τ _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

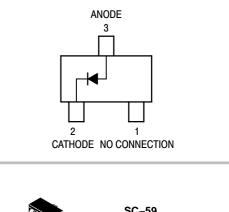
1. t = 1 SEC



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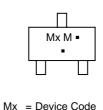
SC-59 PACKAGE SINGLE SILICON SWITCHING DIODES 40/80 V-100 mA SURFACE MOUNT





SC-59 CASE 318D

MARKING DIAGRAM



Mx = Device Code x = A for 151 B for 152 $M = Date Code^*$

= Pb–Free Package

(Note: Microdot may be in either location) *Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

M1MA151AT1, M1MA152AT1

ELECTRICAL CHARACTERISTICS (T_A = 25° C)

Characteristic		Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	M1MA151AT1 M1MA152AT1	I _R	V _R = 35 V V _R = 75 V	-	0.1	μAdc
Forward Voltage		V _F	I _F = 100 mA	-	1.2	Vdc
Reverse Breakdown Voltage	M1MA151AT1 M1MA152AT1	V _R	I _R = 100 μA	40 80	-	Vdc
Diode Capacitance		CD	V _R = 0, f = 1.0 MHz	-	2.0	pF
Reverse Recovery Time (Figure 1)		t _{rr} (Note 2)	$ I_{\rm F} = 10 \ {\rm mA}, \ {\rm V}_{\rm R} = 6.0 \ {\rm V}, \\ {\rm R}_{\rm L} = 100 \ {\Omega}, \ {\rm I}_{\rm rr} = 0.1 \ {\rm I}_{\rm R} $	-	3.0	ns

2. t_{rr} Test Circuit

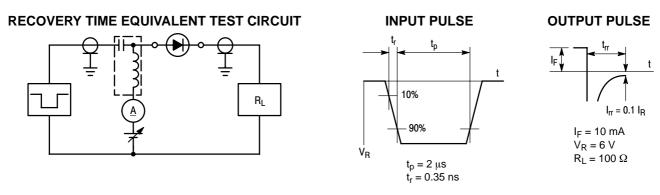


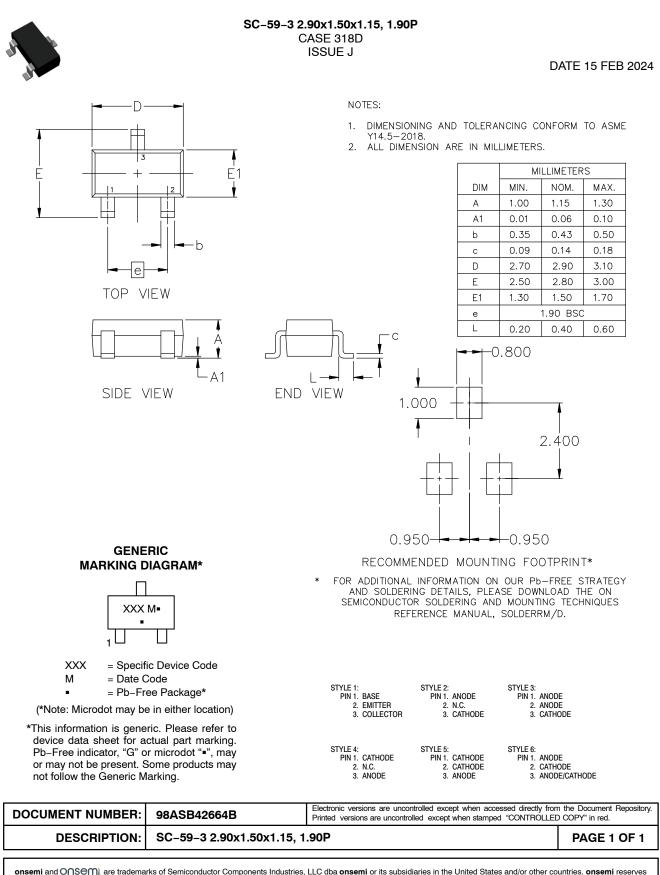
Figure 1. Reverse Recovery Time Equivalent Test Circuit

ORDERING INFORMATION

Device	Package	Shipping [†]	
M1MA151AT1	SC-59		
M1MA151AT1G	SC–59 (Pb–Free)	3000 /Tape & Reel	
M1MA152AT1	SC-59	Suco nape & Reel	
M1MA152AT1G	SC-59 (Pb-Free)		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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